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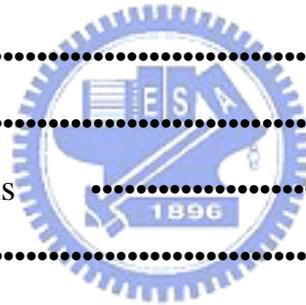
Chapter 3 Investigation of Surface Treatment Prior to Al₂O₃ Gate Dielectric

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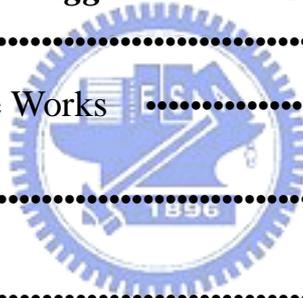## *Chapter 4 Conclusions and Suggestions and Future work*

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Chapter 1

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